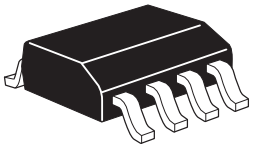
ZXMC3A18DN8
Complementary 30V enhancement mode MOSFET

Summary

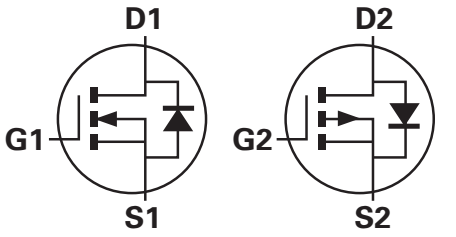
N-Channel = $V_{(BR)DSS}$= 30V : $R_{DS(on)}$= 0.025Ω; I_D= 7.6A

P-Channel = $V_{(BR)DSS}$= -30V : $R_{DS(on)}$= 0.035Ω; I_D= -6.3A



Description

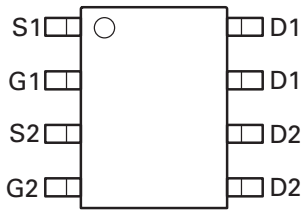
This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



Q1 N-Channel **Q2 P-Channel**

Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package



SO8

Applications

- Motor Drive
- LCD backlighting

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMC3A18DN8TC	13	12	2500

Device marking

ZXMC
3A18

Absolute maximum ratings

Parameter	Symbol	N-channel	P-channel	Unit
Drain-source voltage	V_{DSS}	30	-30	V
Gate-source voltage	V_{GS}	±20	±20	V
Continuous drain current (V_{GS}= 10V; T_{amb}=25°C)[b][d]	I_D	7.6	-6.3	A
(V_{GS}= 10V; T_{amb}=70°C)[b][d]		6.1	-5.0	
(V_{GS}= 10V; T_{amb}=25°C)[a][d]		5.8	-4.8	
Pulsed drain current[c]	I_{DM}	37	-30	A
Continuous source current (body diode)[b]	I_S	3.6	3.2	A
Pulsed source current (body diode)[c]	I_{SM}	37	30	A
Power dissipation at T_{amb} =25°C[a][d]	P_D	1.25		W
Linear derating factor		10		mW/°C
Power dissipation at T_{amb} =25°C[a][e]	P_D	1.8		W
Linear derating factor		14		mW/°C
Power dissipation at T_{amb} =25°C[b][d]	P_D	2.1		W
Linear derating factor		17		mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		°C

Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient[a][d]	$R_{\Theta JA}$	100	°C/W
Junction to ambient[a][e]	$R_{\Theta JA}$	70	°C/W
Junction to ambient[b][d]	$R_{\Theta JA}$	60	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

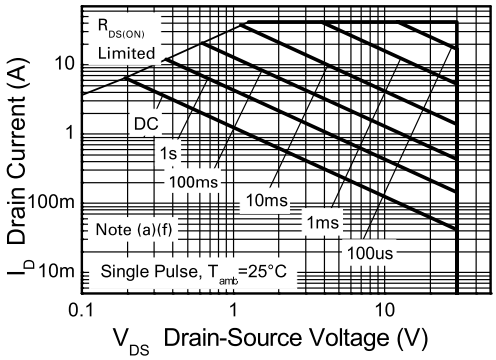
(b) For a device surface mounted on FR4 PCB measured at t ≤10 sec.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Pulse width 300µs, d<= 0.02. Refer to transient thermal impedance graph.

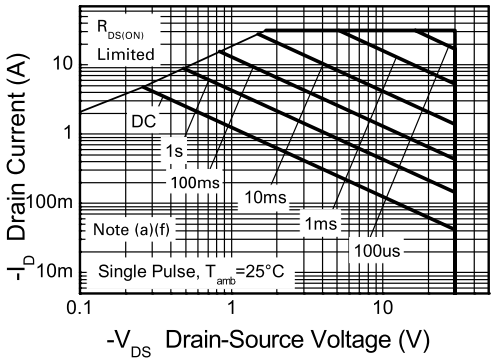
(d) For device with one active die.

(e) For device with two active die running at equal power.

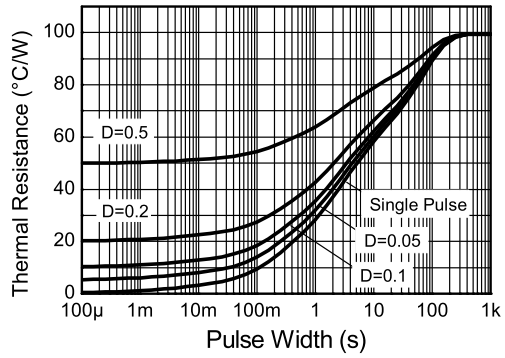
Characteristics



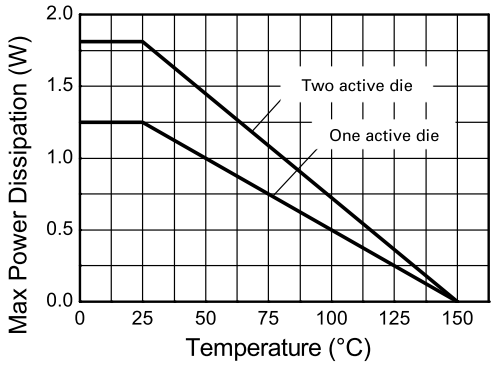
N-channel Safe Operating Area



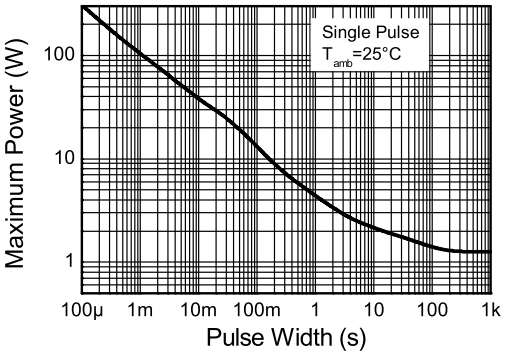
P-channel Safe Operating Area



Transient Thermal Impedance



Derating Curve



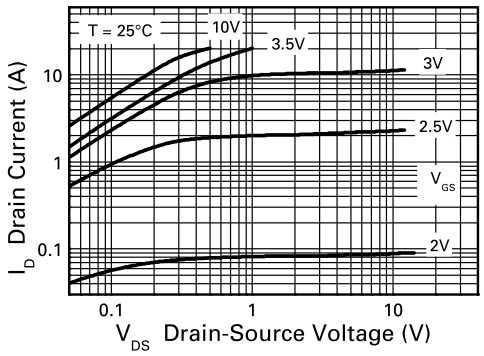
Pulse Power Dissipation

N-channel
Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

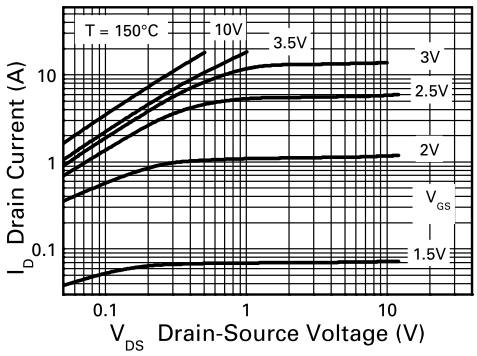
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	30			V	I_D= 250μA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}			0.5	μA	V_{DS}=30V, V_{GS}=0V
Gate-body leakage	I_{GSS}			100	nA	V_{GS}=±20V, V_{DS}=0V
Gate-source threshold voltage	$V_{GS(th)}$	1.0			V	I_D= 250μA, V_{DS}=V_{GS}
Static drain-source on-state resistance (*)	$R_{DS(on)}$			0.025 0.030	Ω	V_{GS}= 10V, I_D= 5.8A V_{GS}= 4.5V, I_D= 5.3A
Forward transconductance(*)(‡)	g_{fs}		17.5		S	V_{DS}= 15V, I_D= 5.8A
Dynamic(‡)						
Input capacitance	C_{iss}		1800		pF	V_{DS}= 25V, V_{GS}=0V f=1MHz
Output capacitance	C_{oss}		289		pF	
Reverse transfer capacitance	C_{rss}		178		pF	
Switching (†) (‡)						
Turn-on-delay time	$t_{d(on)}$		5.5		ns	V_{DD}= 15V, I_D= 6A $R_G \cong 6.0\Omega$, V_{GS}= 10V
Rise time	t_r		8.7		ns	
Turn-off delay time	$t_{d(off)}$		33		ns	
Fall time	t_f		8.5		ns	
Gate charge	Q_g		19.4		nC	V_{DS}= 15V, V_{GS}= 5V I_D= 3.5A
Total gate charge	Q_g		36		nC	V_{DS}= 15V, V_{GS}= 10V I_D= 3.5A
Gate-source charge	Q_{gs}		5.5		nC	
Gate drain charge	Q_{gd}		7.0		nC	
Source-drain diode						
Diode forward voltage(*)	V_{SD}			0.95	V	T_j=25°C, I_S= 6A, V_{GS}=0V
Reverse recovery time(‡)	t_{rr}		20.5		ns	T_j=25°C, I_S= 6A, di/dt=100A/μs
Reverse recovery charge(‡)	Q_{rr}		41.5		nC	

NOTES:
(*) Measured under pulsed conditions. Pulse width ≤300μs; duty cycle ≤2%.
(†) Switching characteristics are independent of operating junction temperature.
(‡) For design aid only, not subject to production testing.

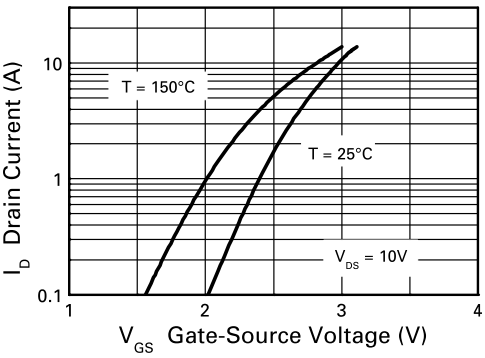
Typical characteristics



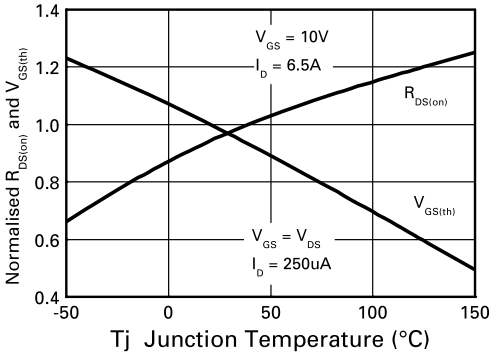
Output Characteristics



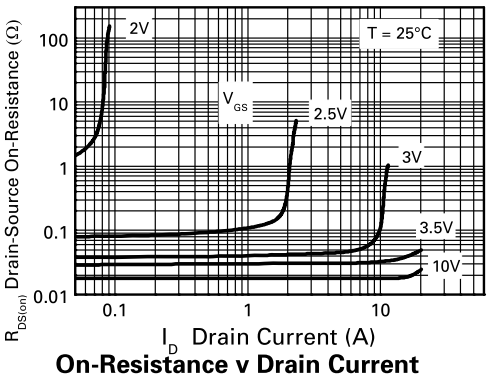
Output Characteristics



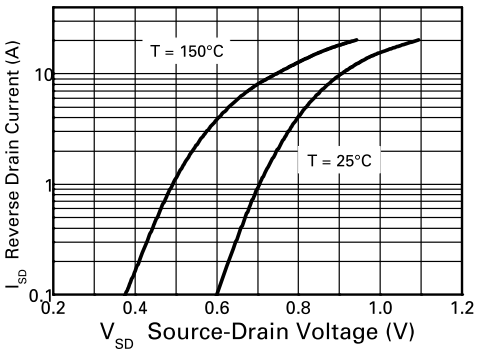
Typical Transfer Characteristics



Normalised Curves v Temperature

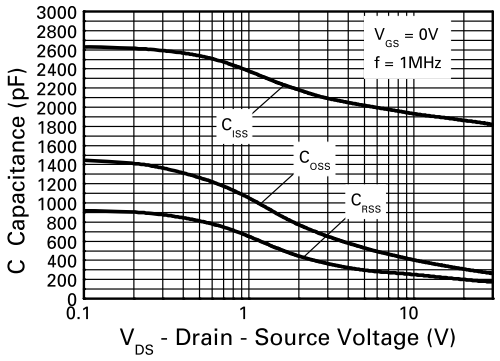


On-Resistance v Drain Current

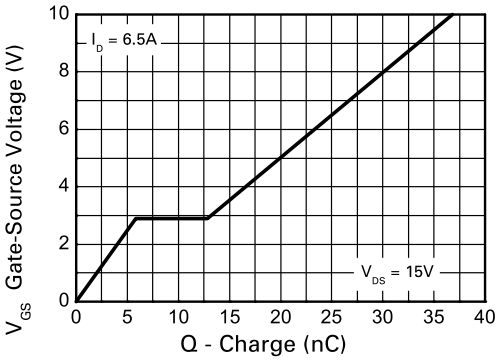


Source-Drain Diode Forward Voltage

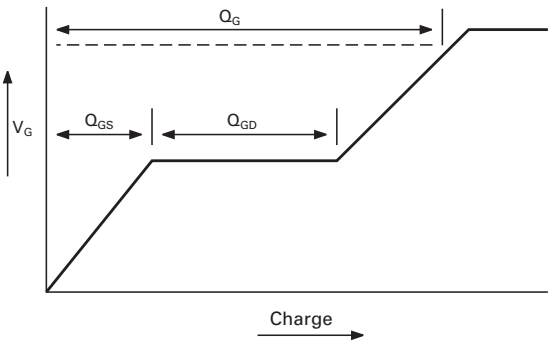
Typical characteristics



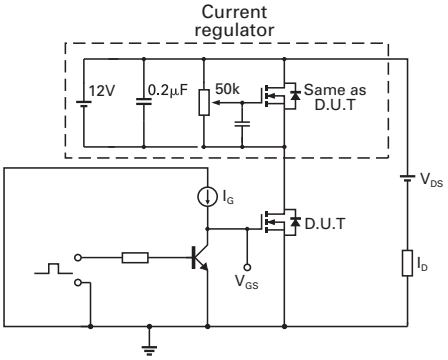
Capacitance v Drain-Source Voltage



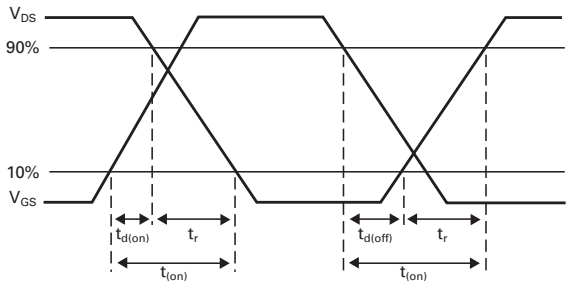
Gate-Source Voltage v Gate Charge



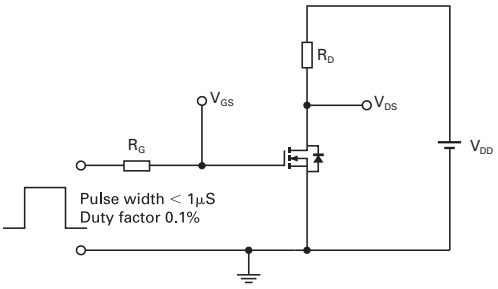
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



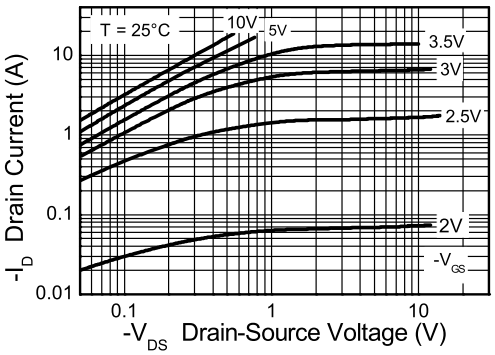
Switching time test circuit

P-channel
Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

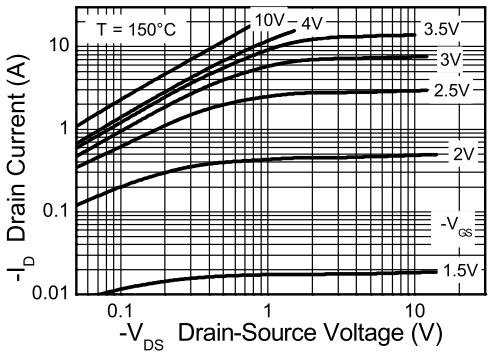
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30			V	I_D= -250μA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}			-1.0	μA	V_{DS}= -30V, V_{GS}=0V
Gate-body leakage	I_{GSS}			100	nA	V_{GS}=±20V, V_{DS}=0V
Gate-source threshold voltage	$V_{GS(th)}$	-1.0			V	I_D= -250μA, V_{DS}=V_{GS}
Static drain-source on-state resistance (*)	$R_{DS(on)}$			0.035 0.050	W	V_{GS}= -10V, I_D= -4.8A V_{GS}= -4.5V, I_D= -4.0A
Forward transconductance(*)(‡)	g_{fs}		8.6		S	V_{DS}= -15V, I_D= -4.8A
Dynamic(‡)						
Input capacitance	C_{iss}		1603		pF	V_{DS}= -15V, V_{GS}=0V f=1MHz
Output capacitance	C_{oss}		434		pF	
Reverse transfer capacitance	C_{rss}		388		pF	
Switching (†) (‡)						
Turn-on-delay time	$t_{d(on)}$		4.8		ns	V_{DD}= -15V, I_D= -1A R_G @ 6.0Ω, V_{GS}= 10V
Rise time	t_r		9.5		ns	
Turn-off delay time	$t_{d(off)}$		60		ns	
Fall time	t_f		38		ns	
Gate charge	Q_g		25		nC	V_{DS}= -15V, V_{GS}= -5V I_D= -4.8A
Total gate charge	Q_g		45		nC	V_{DS}= -15V, V_{GS}= -10V I_D= -4.8A
Gate-source charge	Q_{gs}		5.1		nC	
Gate drain charge	Q_{gd}		11.5		nC	
Source-drain diode						
Diode forward voltage(*)	V_{SD}		0.82	-0.95	V	T_j=25°C, I_S= -3.7 V_{GS}=0V
Reverse recovery time(‡)	t_{rr}		32.5		ns	T_j=25°C, I_S= -2.2, di/dt=100A/μs
Reverse recovery charge(‡)	Q_{rr}		18.4		nC	

NOTES:
(*) Measured under pulsed conditions. Pulse width ≤300μs; duty cycle ≤2%.
(†) Switching characteristics are independent of operating junction temperature.
(‡) For design aid only, not subject to production testing.

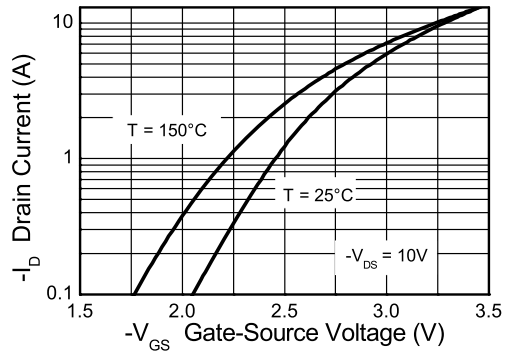
Typical characteristics



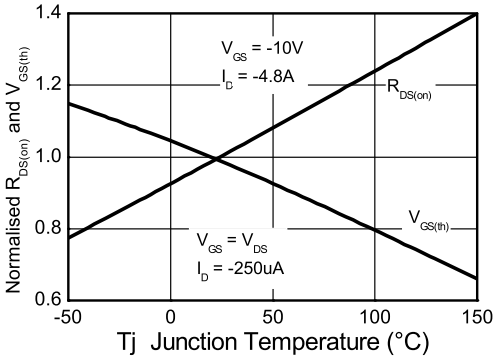
Output Characteristics



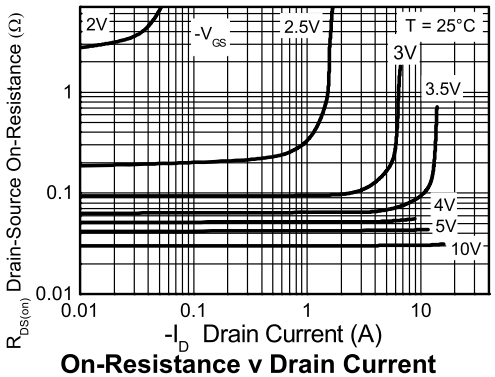
Output Characteristics



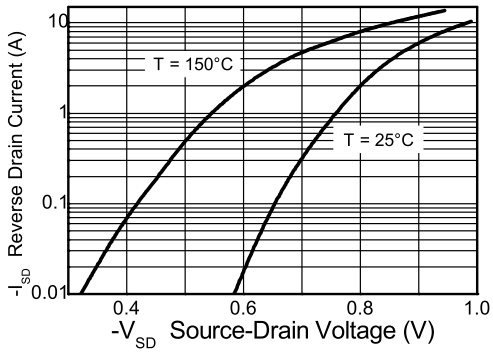
Typical Transfer Characteristics



Normalised Curves v Temperature

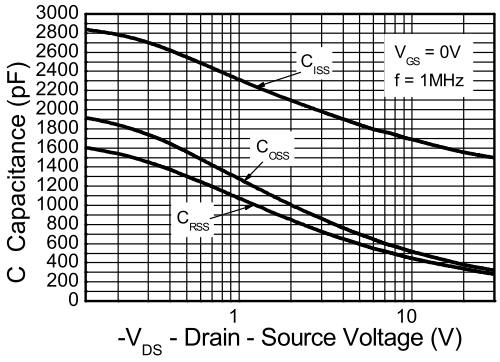


On-Resistance v Drain Current

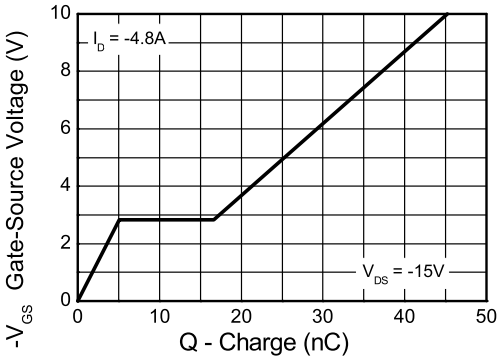


Source-Drain Diode Forward Voltage

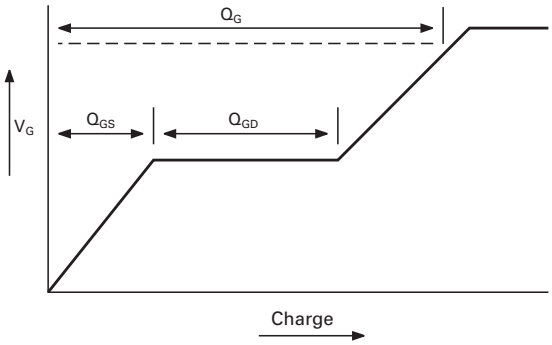
Typical characteristics



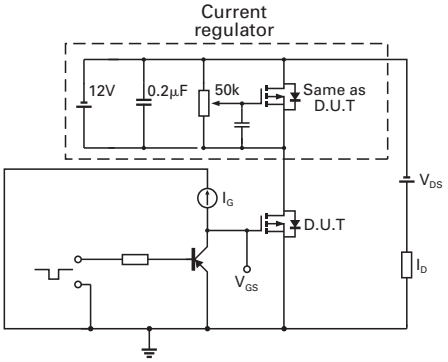
Capacitance v Drain-Source Voltage



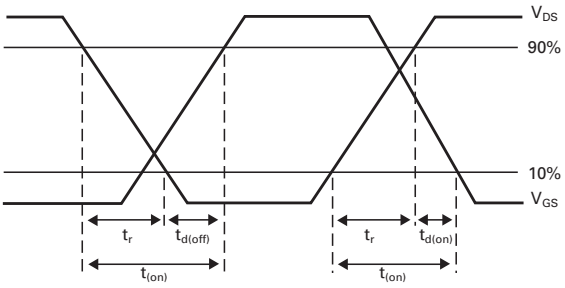
Gate-Source Voltage v Gate Charge



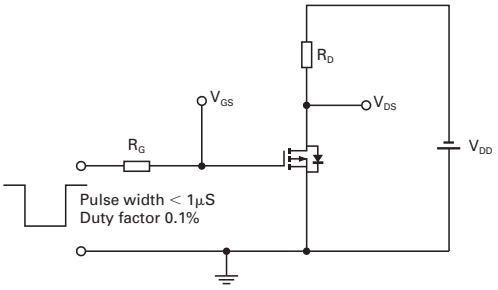
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

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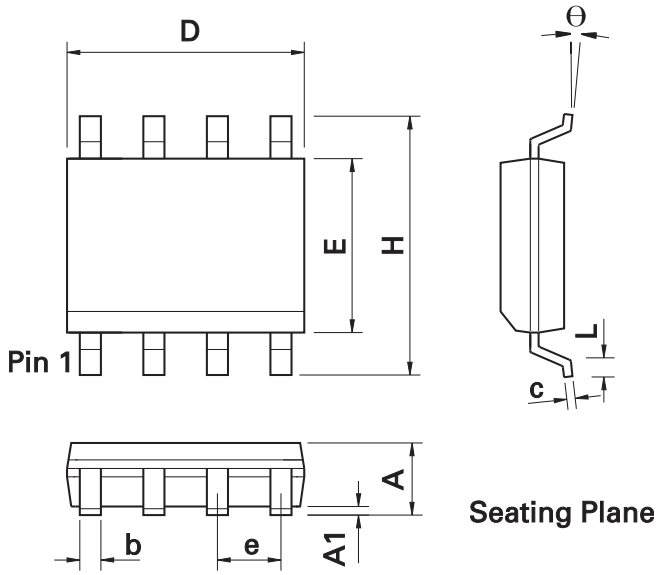
Package outline - SO8



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	Θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

Definitions

Product change

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   1. are intended to implant into the body

or

   2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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ESD (Electrostatic discharge)

Semiconductor devices are susceptible to damage by ESD. Suitable precautions should be taken when handling and transporting devices. The possible damage to devices depends on the circumstances of the handling and transporting, and the nature of the device. The extent of damage can vary from immediate functional or parametric malfunction to degradation of function or performance in use over time. Devices suspected of being affected should be replaced.

Green compliance

Zetex Semiconductors is committed to environmental excellence in all aspects of its operations which includes meeting or exceeding regulatory requirements with respect to the use of hazardous substances. Numerous successful programs have been implemented to reduce the use of hazardous substances and/or emissions.

All Zetex components are compliant with the RoHS directive, and through this it is supporting its customers in their compliance with WEEE and ELV directives.

Product status key:

"Preview"	Future device intended for production at some point. Samples may be available
"Active"	Product status recommended for new designs
"Last time buy (LTB)"	Device will be discontinued and last time buy period and delivery is in effect
"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

Datasheet status key:

"Draft version"	This term denotes a very early datasheet version and contains highly provisional information, which may change in any manner without notice.
"Provisional version"	This term denotes a pre-release datasheet. It provides a clear indication of anticipated performance. However, changes to the test conditions and specifications may occur, at any time and without notice.
"Issue"	This term denotes an issued datasheet containing finalized specifications. However, changes to specifications may occur, at any time and without notice.

Zetex sales offices

Europe	**Americas**	**Asia Pacific**	**Corporate Headquarters**
Zetex GmbH Kustermannpark Balanstraße 59 D-81541 München Germany	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com